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CORRECTION

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Correction: High-performance optoelectronic memory based on bilayer MoS_2 grown by Au catalyst

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Correction for 'High-performance optoelectronic memory based on bilayer MoS_2 grown by Au catalyst' by Fengyou Yang *et al.*, *J. Mater. Chem. C*, 2020, **8**, 2664–2668.

The author regret an error in Fig. 4d of the published article; the corrected version of Fig. 4d is shown here. The rest of Fig. 4 and the caption are unchanged.

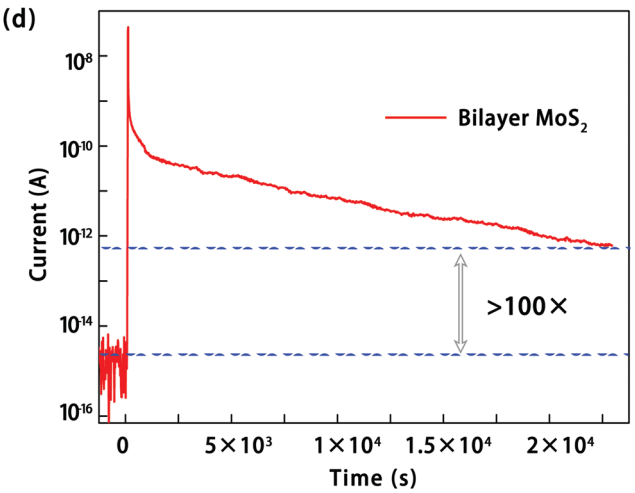

Fig. 4 (d) The retention time property of the bilayer MoS_2 optoelectronic memory.

Please note that these changes do not affect the results and conclusions reported in the article.
The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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